

ABSTRACT OF THE DISCLOSURE

The present invention has an object to provide a MOS type transistor with a simple process, in which a high concentration junction can be stably formed so shallowly as to prevent a high concentration region constituting a drain/source region from extending beyond a contact hole due to a production variation, which cannot be attained by a conventional MOS type transistor of an LDD structure. The present invention having the following feature. That is, in forming the contact hole of the MOS type transistor, a nitride film is used as an etch-stop film to keep an Si substrate from being overetched. By using the contact hole as a mask, ion implantation is carried out to form the high concentration diffusion region constituting the source/drain region.